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DRD3

Study of Deep Carbonated LGAD at IHEP

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Outline

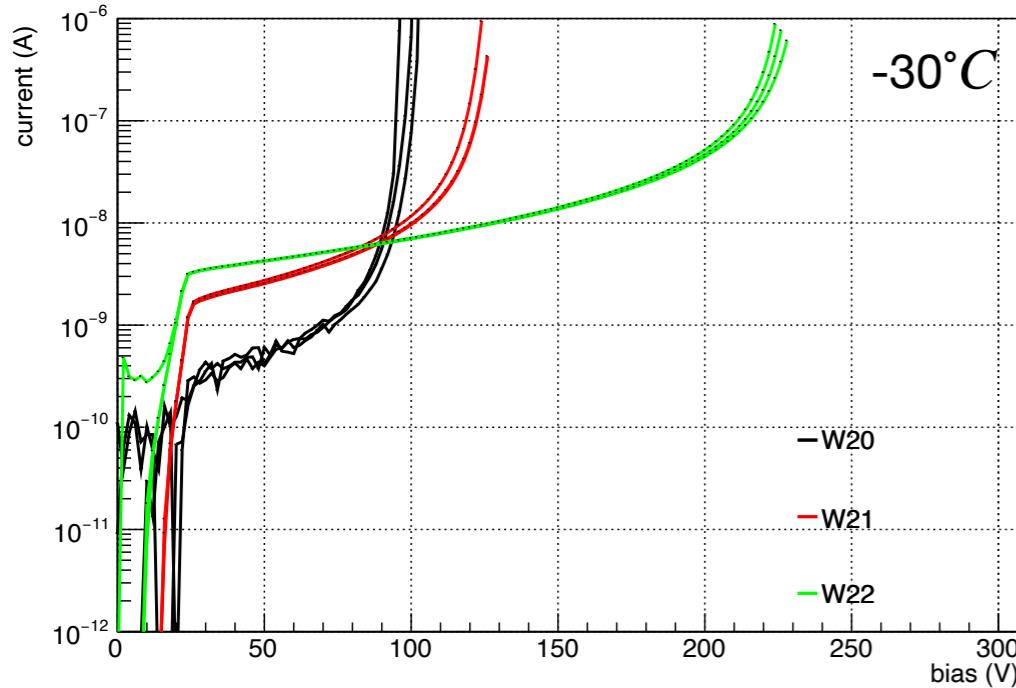
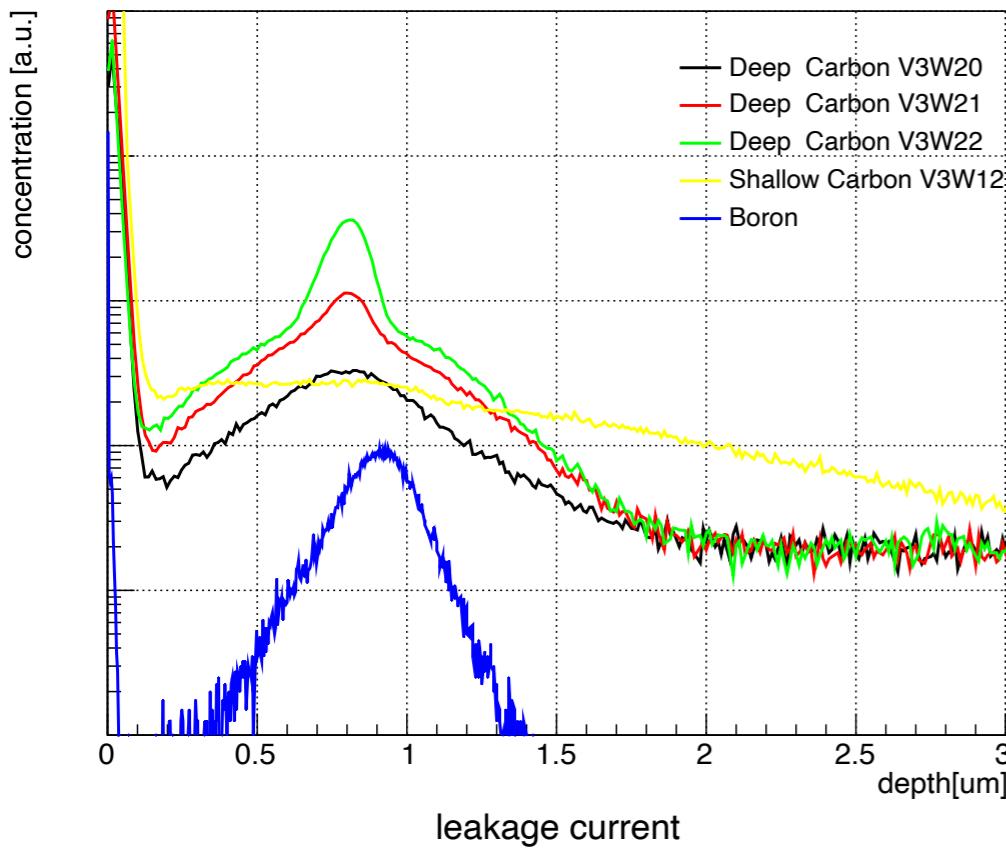
- Motivation
- General features
- Neutron irradiation
- Proton irradiation
- Comparison and conclusion

Motivation

- Growing need for enhanced radiation hardness in detectors:
 - Low operation bias to suppress single event burnt down.
 - Survive from higher accumulated irradiation dose.
- Low gain avalanche detectors designed by IHEP shows good radiation tolerance.These detectors are:
 - Carbonated.
 - Different implantation depth for gain layer and Carbon.
 - High thermal load for Carbon.
- Explore different strategy with deeper implantation energy for Carbon.

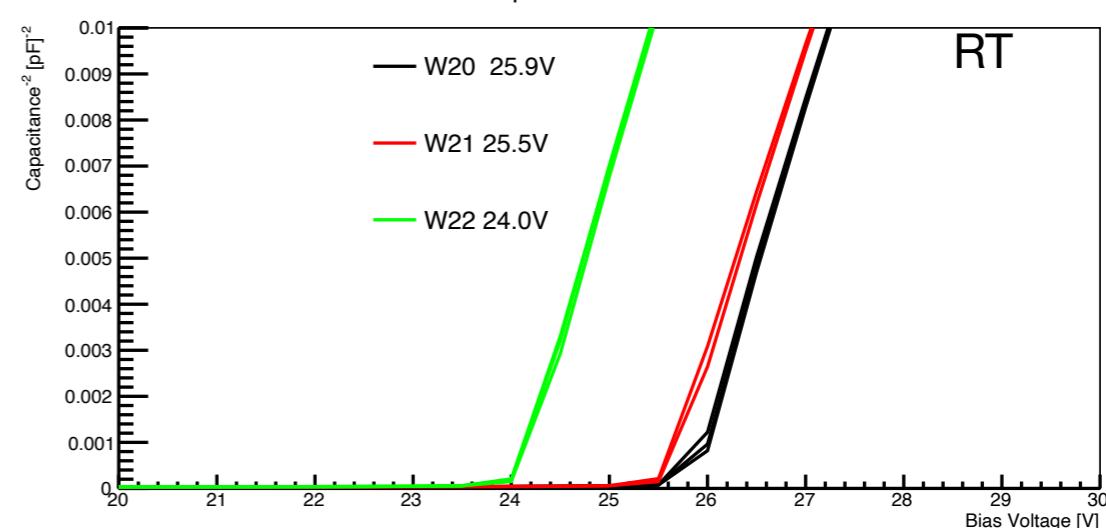
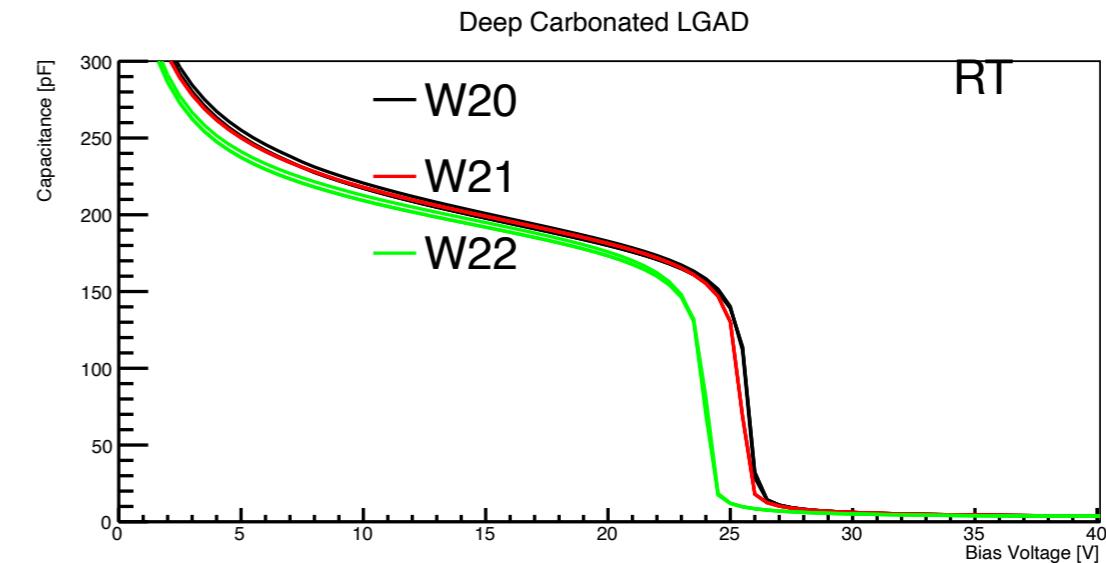
General features before irradiation

SIMS profile



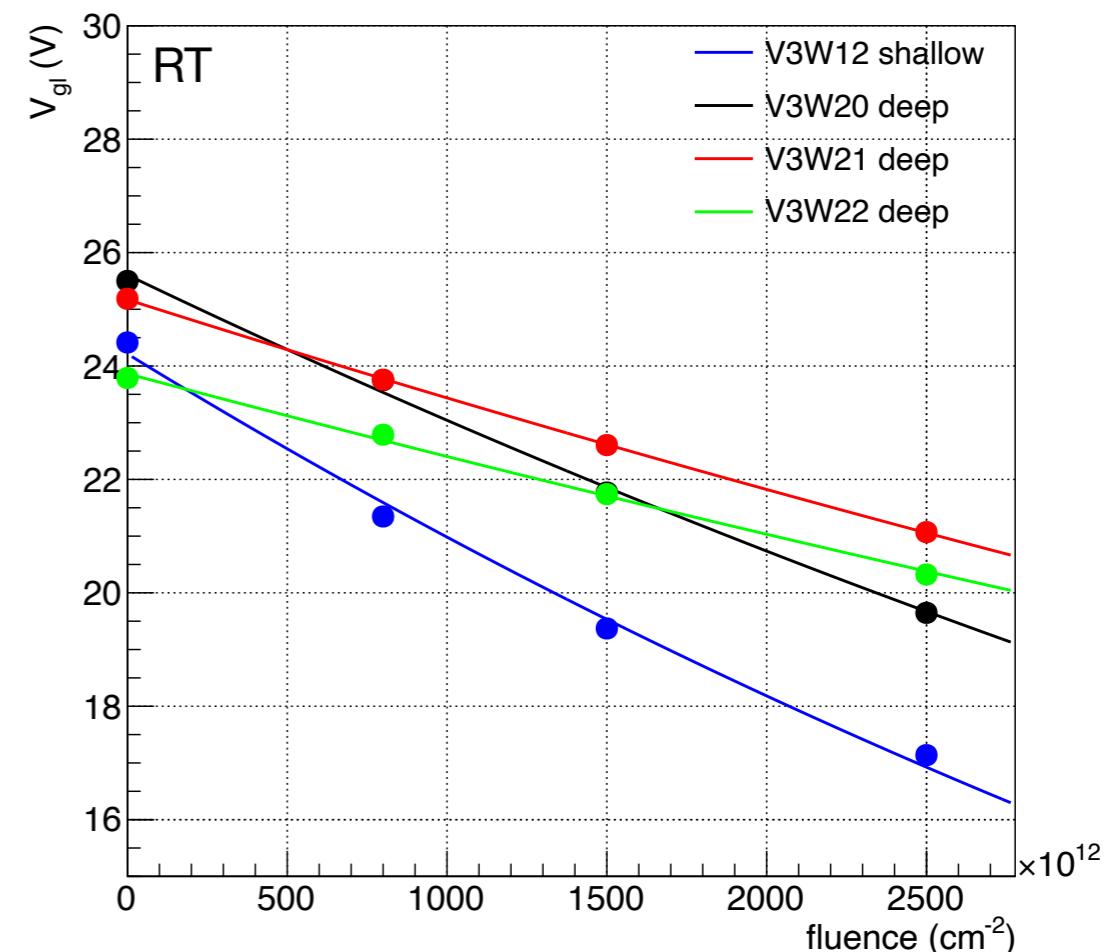
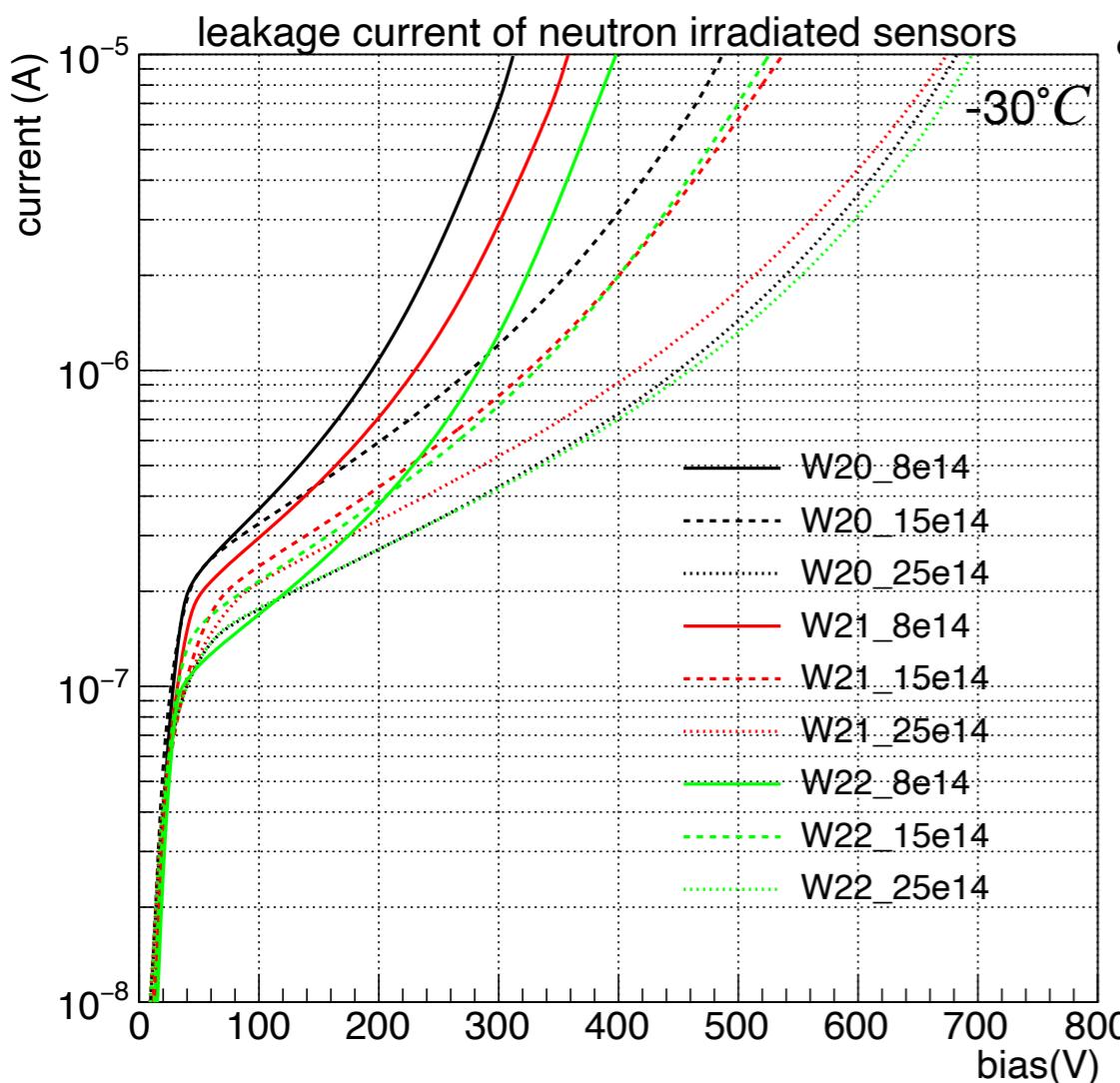
	W20	W21	W22
V _{gl} (V)	25.9	25.5	24 (-7%)
V _{bд} (V) (200nA)	100	120	220
Carbon dose (a.u.)	2	5	10

- W20 W21 and W22
 - Same Boron implantation depth and dose.
 - Same Carbon depth (close to boron) with different dose.
 - Leakage current (at -30°C) and the breakdown voltage increase with Carbon density.
 - An initial acceptor deactivation is observed in W21 and W22.



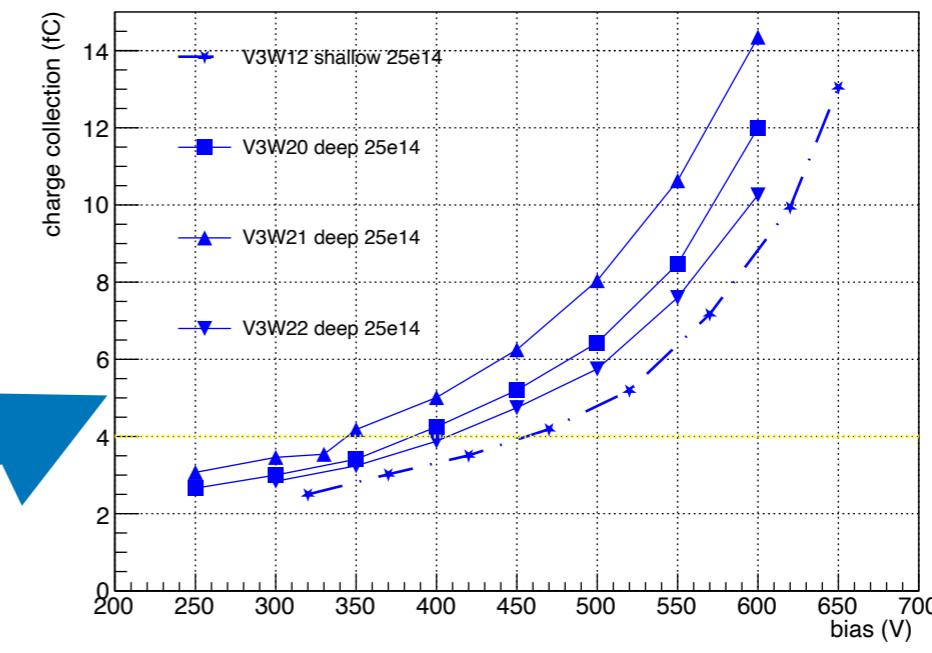
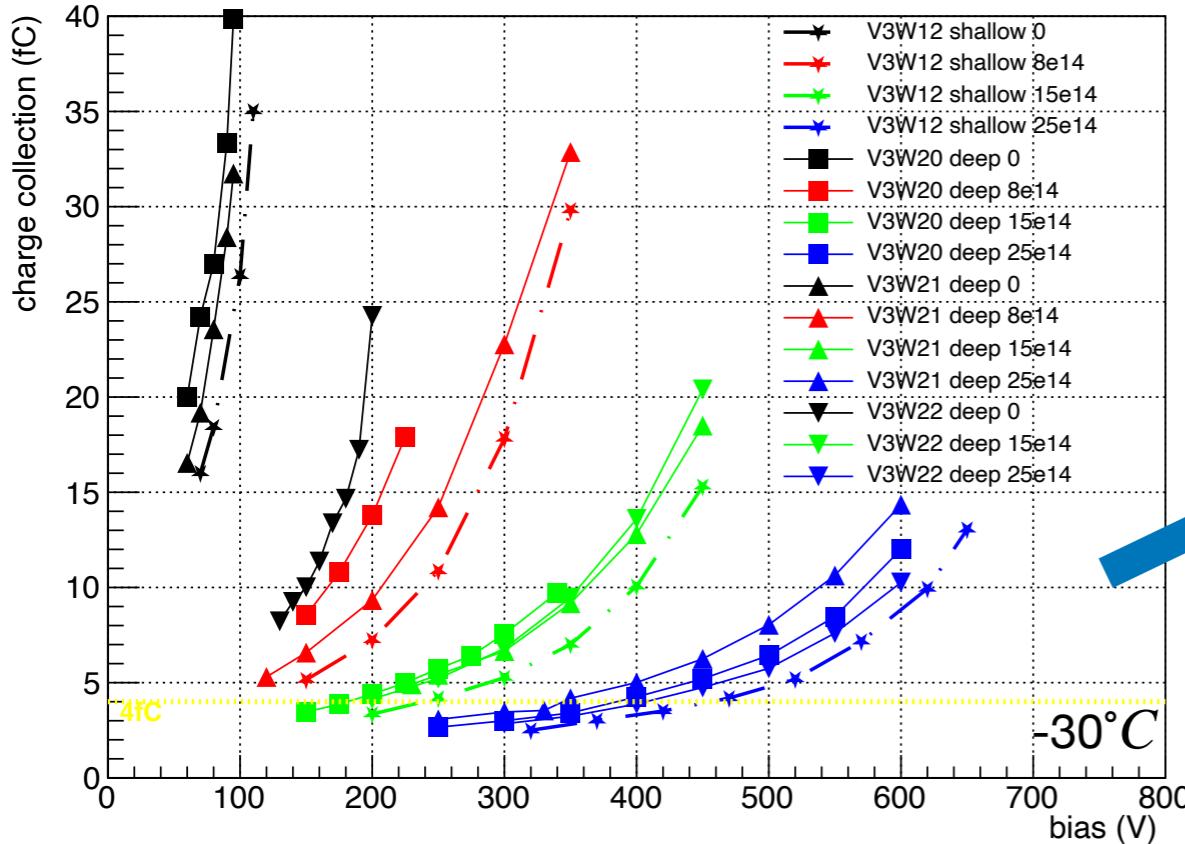
Electronic features of neutron irradiated sensors

- The leakage current difference gradually become smaller as irradiation dose increase.
- A deactivation observed at the beginning; W22 has the lowest removal factor.

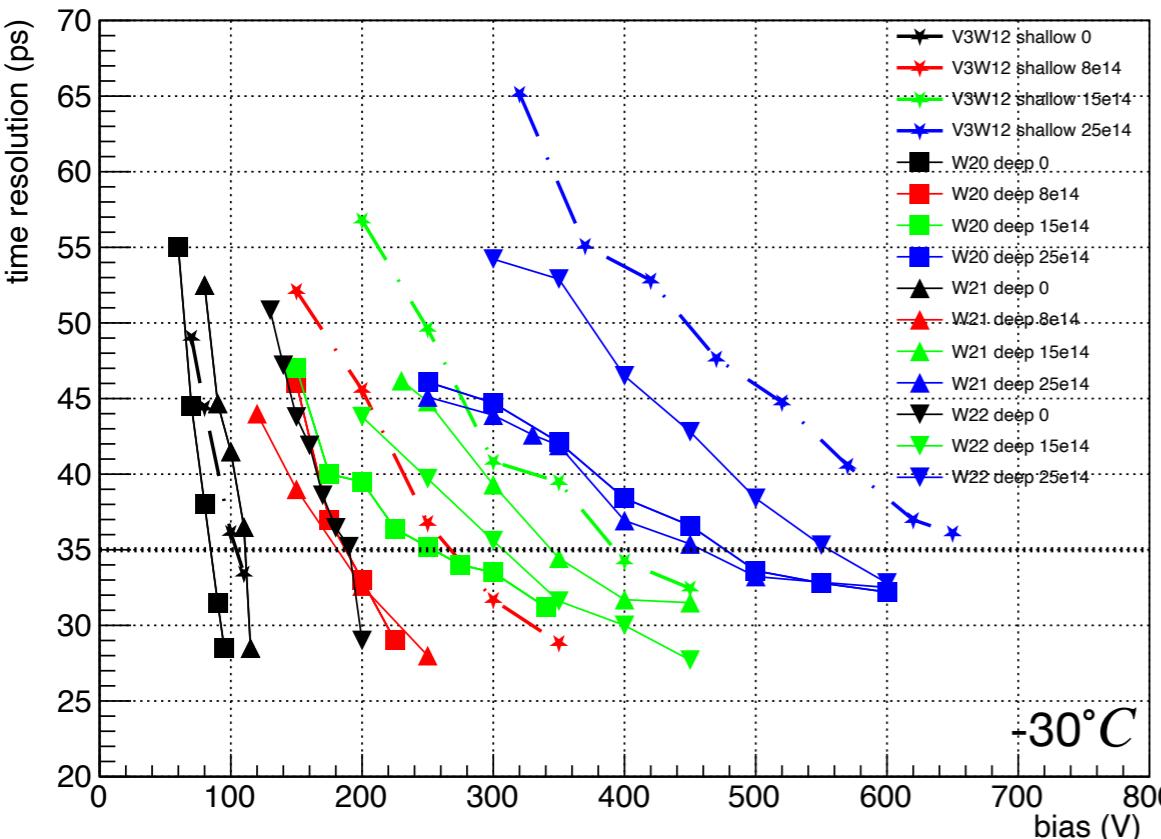


	W12	W20	W21	W22
Removal factor ($\times 10^{16} \text{ cm}^2$)	1.31 1.05 0.71 0.63			

Electronic features of neutron irradiated sensors



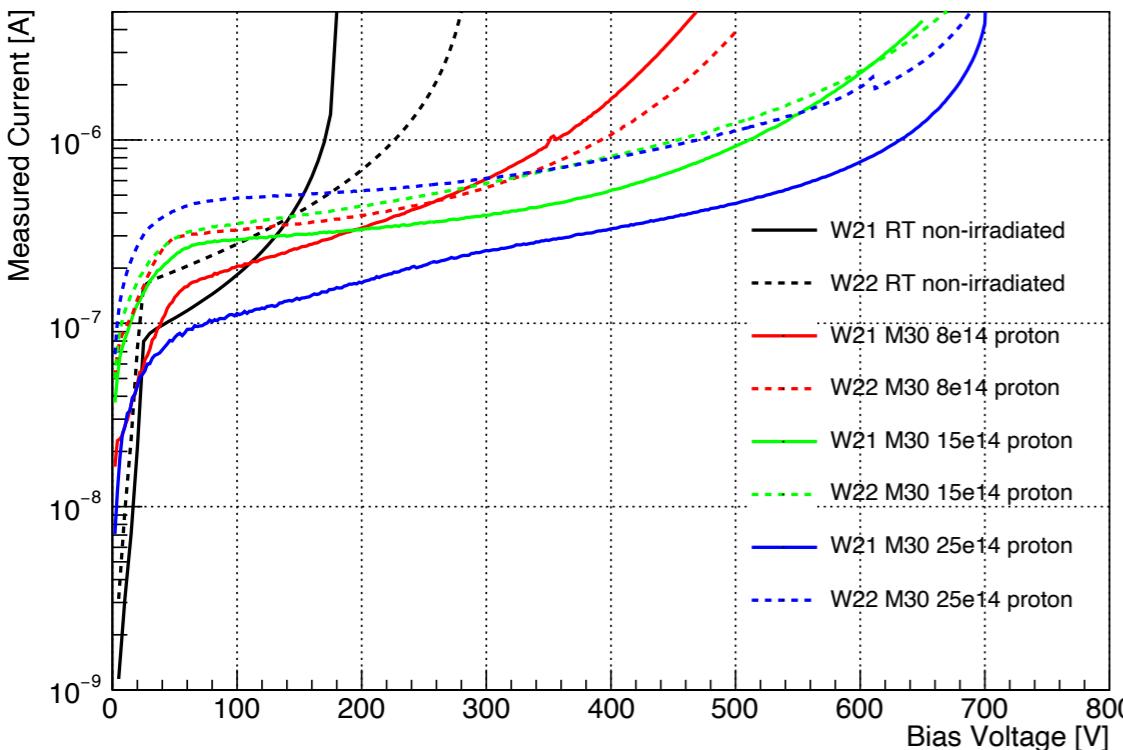
Wafer	W20	W21	W22	W12
4fC bias	380 V	340 V	410 V	460 V



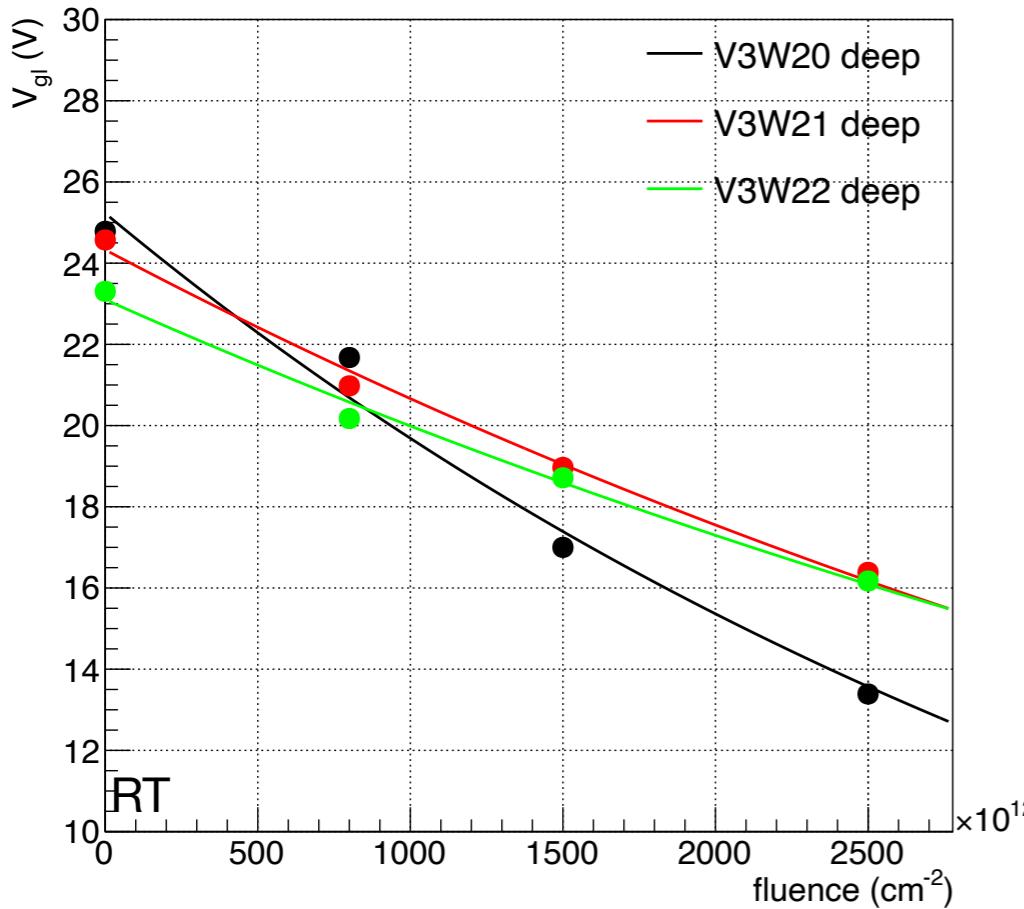
- 4 (3 deep Carbon + 1 shallow Carbon) with same Boron layer.
 - Deep Carbon overall better than shallow Carbon.
 - W20 and W21 are close, W22 needs a higher bias voltage at the very beginning (due to deactivation).
 - The sensors performance don't directly decided by the removal factor.

Electronic features of proton irradiated sensors

IV

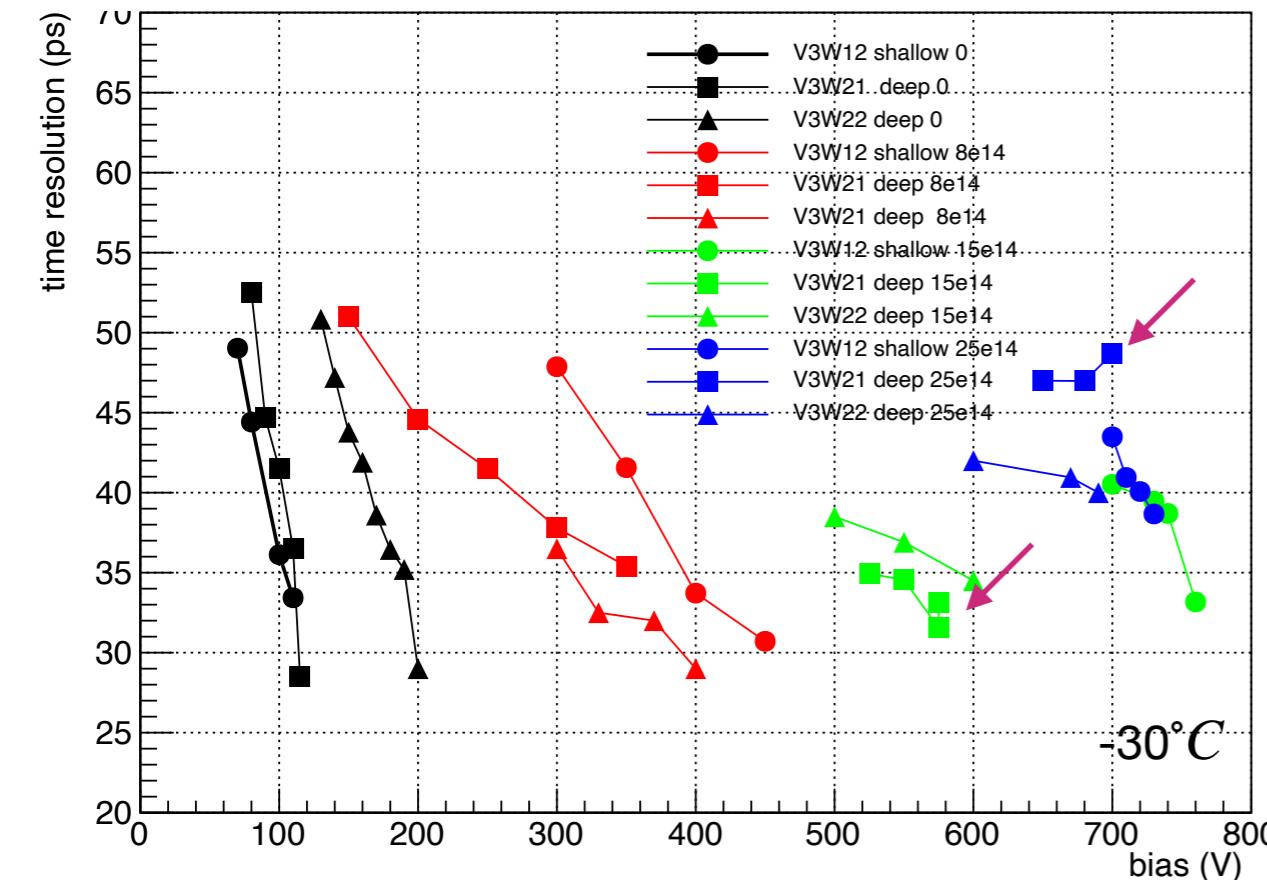
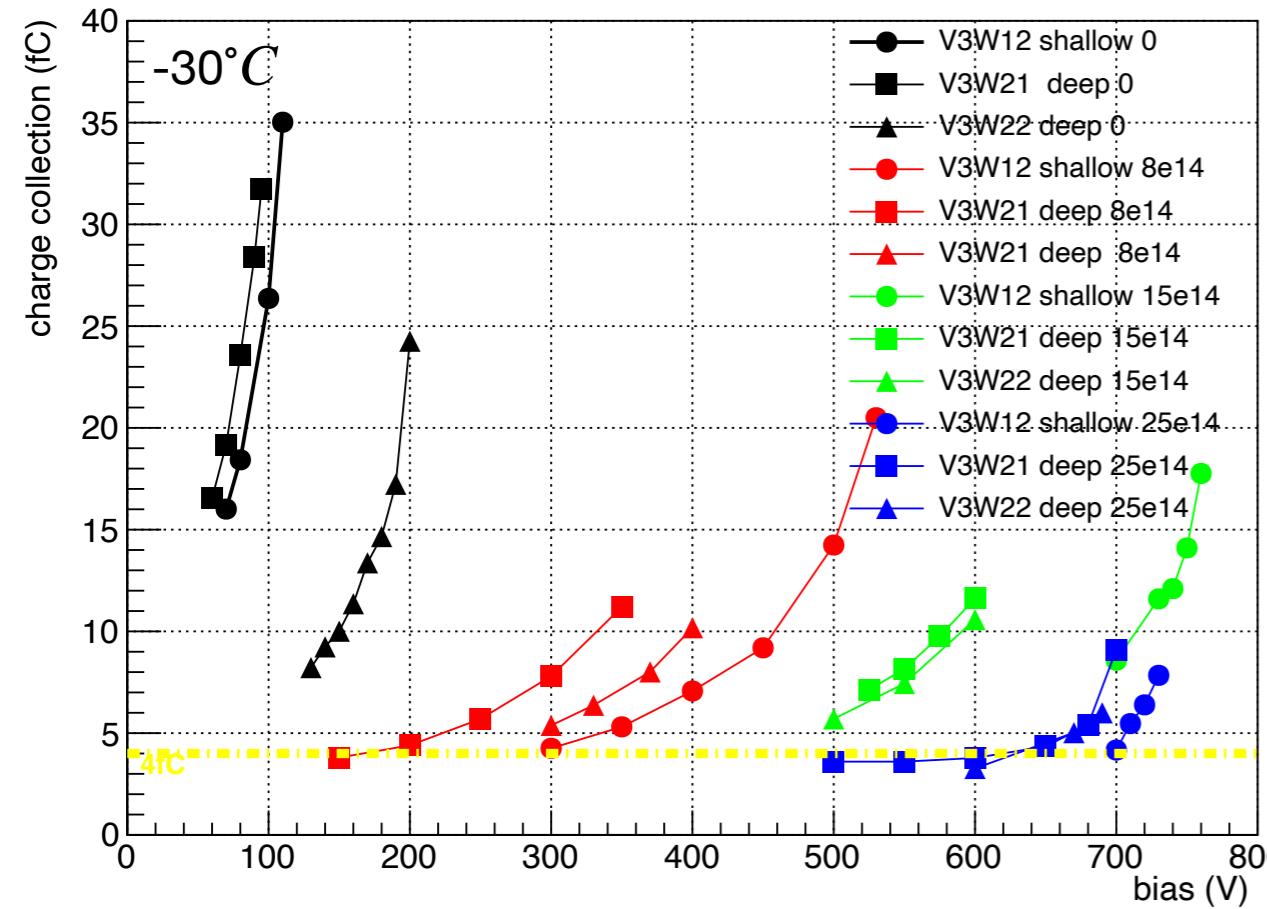


- Irradiated with 80MeV proton (hardness factor ~ 1.58) with n_{eq} up to $25e14/cm^2$.
- W22 leakage current greater than W21 before/after irradiation.
- Order of removal factors same as neutron irradiation case, with large absolute value.



	W20	W21	W22	
Proton Removal factor ($\times 10^{16} \text{ cm}^2$)		2.48	1.63	1.44
Neutron Removal factor ($\times 10^{16} \text{ cm}^2$)	1.05	0.71	0.63	

Electronic features of proton irradiated sensors



3 (2 deep carbon + 1 shallow carbon) with same boron layer.

- Deep carbon overall better than shallow carbon.
- At low irradiation dose, the advantage of deep ones are clear while for extremely high irradiation dose, the difference is narrowed, both W21/W22 and W12 need $>600\text{V}$ to get a moderate charge collection.
- Up to very high irradiation dose, the time resolution increase with bias.

A comparison of proton and neutron irradiation results

	W20	W21	W22
Proton Removal factor (x1e16 cm²)	2.48	1.63	1.44
Neutron Removal factor (x1e16 cm²)	1.05	0.71	0.63
C_p/C_n	2.36	2.30	2.29

- For 80MeV proton irradiation and reactor neutron irradiation, an average c_p/c_n of 2.32 is obtained.
- With the increase of carbon density, decrease of removal factor is obtained from both neutron and proton irradiation.
- However, W22 with the lowest factor can not obtain a best charge collection/temporal resolution.

Summary

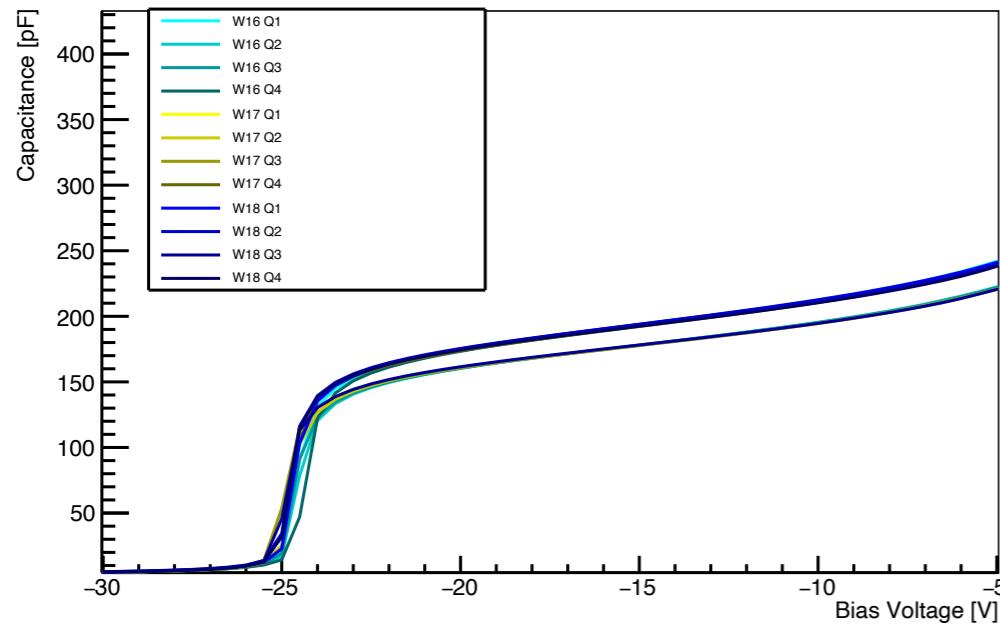
- LGAD with gain layer and carbon implanted in a similar depth was studied.
 - Improvements results from a higher carbon density benefits the removal factors and cc/tr.
 - The Carbon also leads to suppressing the gain layer active Boron, while the c factors might remain low, the cc/tr can be worsen(from W22).

BackUp

Vgl of shallow/deep carbon sensors

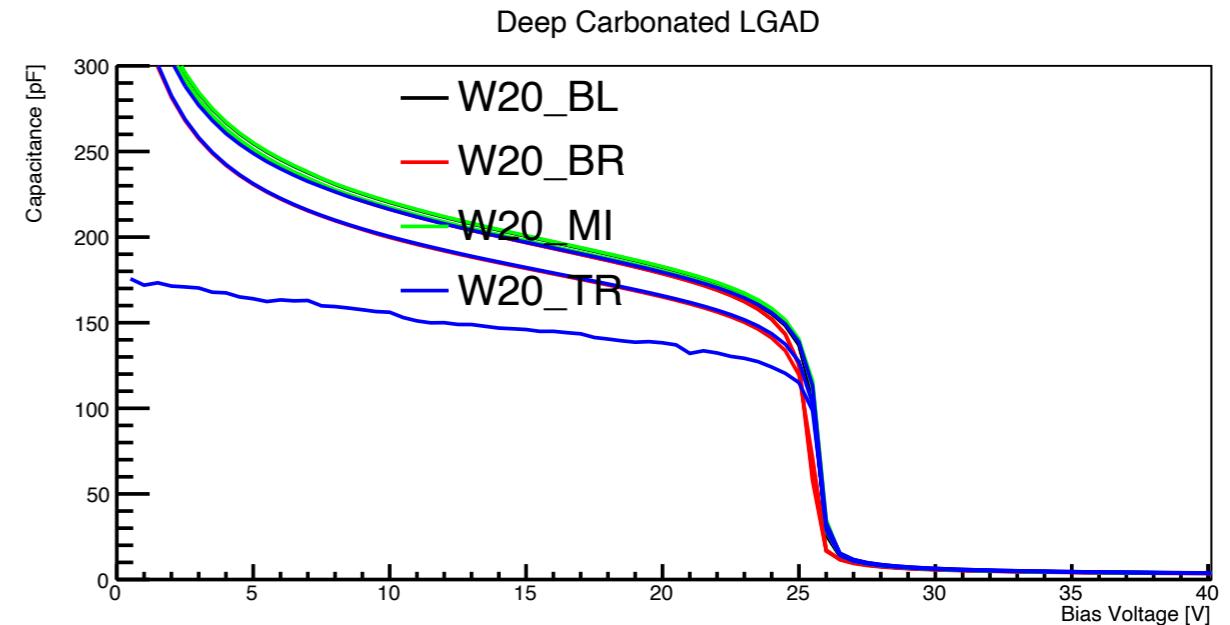
Shallow

W16 W17 W18

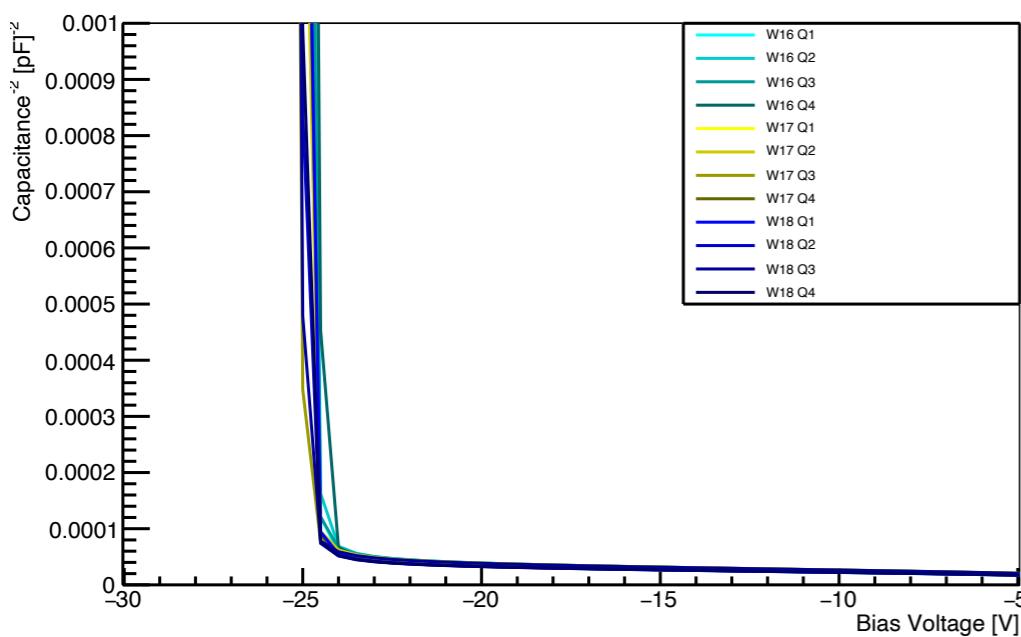


Deep

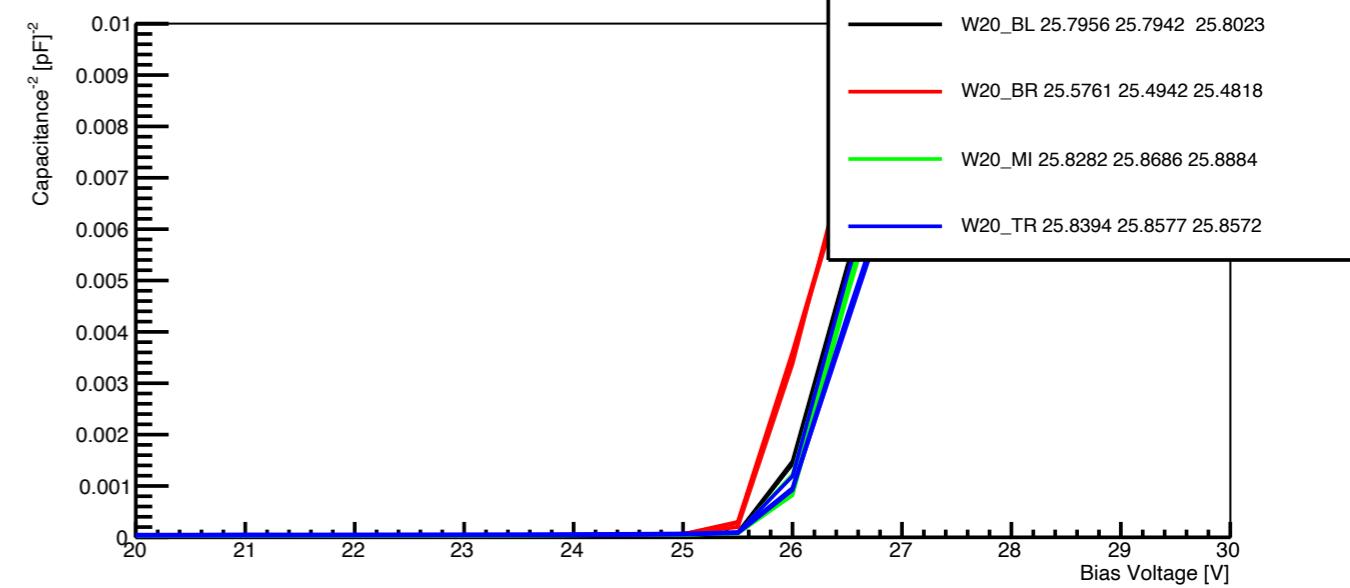
Deep Carbonated LGAD



W16 W17 W18

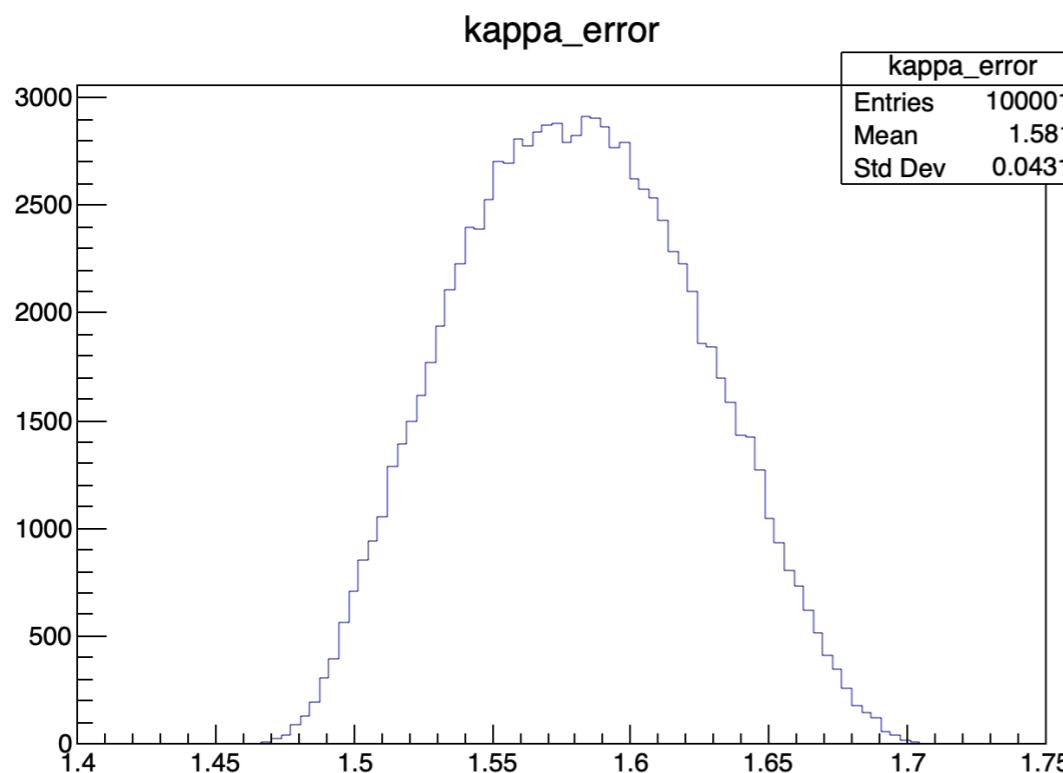


Deep Carbonated LGAD



Hardness factor

Device	PIN1	PIN2	PIN3
Fluence (p/cm ²)	7.59E+12	6.07E+14	1.14E+15
V _{fd} (V)	5	25	50
I _{leak} (Average)	3.7E-08	3.16E-06	6.19E-06
I _{leak} range	4v-10v	20v-30v	40v-60v



- The hardness factor (or κ) is 1.581 on average (1.47-1.71), which is 13% higher than the NIEL value we used when calculating c factor.